

Theory of Magneto-resistance of Disordered Superconducting Films

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(Dated: February 2, 2008)

Recent experimental studies of magneto-resistance in disordered superconducting thin films reveal a huge peak (about 5 orders of magnitude). While it may be expected that magnetic field destroys superconductivity, leading to an enhanced resistance, attenuation of the resistance at higher magnetic fields is surprising. We propose a model which accounts for the experimental results in the entire range of magnetic fields, based on the formation of superconducting islands due to fluctuations in the superconducting order parameter amplitude. At strong magnetic fields Coulomb blockade in these islands gives rise to negative magneto-resistance. As the magnetic field is reduced the effect of Coulomb blockade diminishes and eventually the magneto-resistance changes sign. Numerical calculations show good qualitative agreement with experimental data.

PACS numbers: 71.30.+h, 73.43.-f, 73.43.Nq, 74.20.Mn

The interplay between superconductivity and disorder is a long-standing problem, dating back to the late fifties [1, 2], resulting in the common wisdom that weak disorder has no dramatic effect on superconductivity. Strong disorder, however, may have a profound effect, driving the system from a superconducting (SC) to an insulating state. Such a SC-insulator transition (SIT) was observed in two-dimensional amorphous superconducting films [3]. Reducing the film thickness or an increasing perpendicular magnetic field drives these films (which are held below their bulk critical temperature) from a SC state, characterized by a vanishing resistance as $T \rightarrow T_c$, to an insulating state, characterized by a diverging resistance as $T \rightarrow 0$. The possibility of tuning the system continuously between these two phases is a manifestation of a quantum phase transition [4].

The origin of this transition is still in debate. While some theories [5] claim that it may be understood in terms of Cooper-pair scattering out of the SC condensate into a Bose-glass state (so-called "dirty boson" models), there is evidence, both experimental [6, 7, 8, 9] and theoretical [10], that a percolation description of the SIT is more adequate for, at least, some of these samples.

More insight into the nature of the SIT may be gained by looking at the magneto-resistance (MR) on its insulating side. Decade-old experiments observed non-monotonic MR, exhibiting a shallow peak at some magnetic field $B_{\max}$ [11, 12]. Recent experiments [13] show, however, that in some samples the effect is dramatic, with the resistance value at the peak, $R_{\max}$, reaching as high as a few orders of magnitude its value at the SIT. As the magnetic field is further increased the MR drops back a few orders of magnitude (inset of Fig. 3). Further investigations of this effect [14] reveal that disorder also has a major influence. With increasing disorder strength, the critical field for the SIT, B_c , diminishes, while $R_{\max}$ increases. The temperature dependence of the MR at high temperatures fits an activation-like be-

havior, $R \propto \exp(T_0/T)$, with a magnetic field dependent T_0 as seen in the inset of Fig. 4(a). At lower temperatures there is a deviation from this behavior towards some weaker temperature dependence. While an enhancement of the resistance with increasing magnetic field may be understood in terms of decreasing SC order, the suppression of the resistance with further increase of magnetic field remains a puzzle.

Here we propose a model for the MR in the entire range of magnetic fields. The model is based on three assumptions. The first is that disorder induces formation of SC islands (SCIs) due to fluctuations in the amplitude of the SC order parameter. This concept has already been used to interpret some experiments [11, 13]. It was directly observed in other systems by STM measurements [15] and further corroborated by numerical simulations [16]. The second assumption is that as the magnetic field is increased, the concentration and size of these SCIs decrease. Preliminary numerical results support this picture and will be reported in the future. The third assumption is that the SCIs have a charging energy, and thus, a Cooper pair entering the SCI via an Andreev tunneling process, has to overcome the charging energy. The charging energy is expected to be inversely proportional to the island size, and thus to increase with increasing magnetic field.

In order to see the mechanism by which the MR can be negative, consider such a system in the strong magnetic field regime, $B \gg B_{\max}$ (Fig. 1(a)). Due to the strong magnetic field the SCIs are small and have a large charging energy. There are two types of trajectories available for electron transport: those which follow normal areas of the sample ("normal paths", solid lines in Fig. 1(a)) and those in which an electron tunnels into a SCI via the Andreev channel ("island paths", dashed lines in Fig. 1(a)). The resistance of the normal paths has some value (which may depend on e.g. length, temperature, etc.) and is assumed to be only weakly affected by magnetic field.

Due to the Coulomb blockade, transport through the SCI paths is thermally activated, and hence the resistance of the island paths is of the form $R \sim \exp(E_c/T)$, where E_c is the charging energy of the island. If E_c is large then the main contribution to the conductance is due to transport along the normal paths. Consistent with experiment, the MR in this regime is small.

As the magnetic field is decreased (but still in the regime $B > B_{\max}$, Fig. 1(b)), more SCIs are created and their size increases, but they are still small enough such that transport along normal paths is favorable. However, some paths which were normal at higher fields (e.g. bottom solid line in Fig. 1(a)) now become island paths and hence unavailable for electron transport (bottom dashed line in Fig. 1(b)). Thus, the effective phase space available for electron transport diminishes, resulting in a negative MR. Eventually, at a certain magnetic field $B = B_{\max}$ (Fig. 1(c)) some SCIs are large enough so that their charging energy is small and the resistance through them is comparable to the resistance through normal paths. At this point the resistance reaches its maximum value, since as the magnetic field is further decreased (Fig. 1(d)) the SCIs are so large that transport through them is always preferred over transport through normal paths. Increase in number and size of the SCIs will thus result in a decrease in the resistance. At the critical field B_c the SCIs percolate through the system, resulting in an insulator-to-SC transition. We note that if the temperature is smaller than the Josephson coupling between two islands then SC correlations will extend between them, effectively joining them to a single island. Thus, we expect that at low temperatures the geometry will be temperature-dependent, resulting in a temperature-dependent critical point as is indeed seen in some experiments.

In order to substantiate these heuristic arguments we model the thin film by a square lattice, where each site can be either normal, with probability p , or SC, with probability $1 - p$, corresponding to the concentration of normal areas and SCIs in the sample. The probability p is a function of the magnetic field B , and we may assume that $p(B)$ is an increasing monotonic function. To describe the disordered system in strong magnetic fields, in the absence of SCIs, we follow Ref. [17] and assign a resistance between any two normal sites of the form

$$R_{NN} = R_0 \exp \left(\frac{2r_{ij}}{\xi_{loc}} + \frac{|\epsilon_i| + |\epsilon_j| + |\epsilon_i - \epsilon_j|}{2kT} \right), \quad (1)$$

where R_0 is a constant, r_{ij} is the distance between sites i and j , ξ_{loc} is the localization length, ϵ_i is the energy of the i -th site measured from the chemical potential (taken from a uniform distribution $[-W/2, W/2]$) and T is the temperature. The localization length ξ_{loc} is taken to be small (in units of lattice constant), effectively allowing only nearest- and next-nearest-neighbor hopping. All SC sites that are linked to each other are considered a single

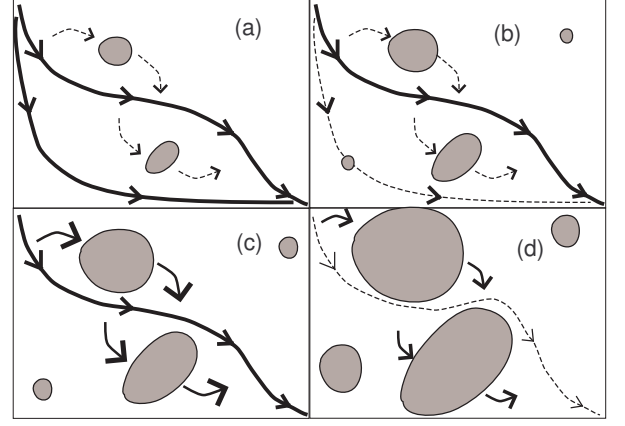


FIG. 1: Schematic representation of the model : (a) At strong magnetic fields, $B \gg B_{\max}$, The system is composed of small superconducting islands with large charging energy. In this regime transport through normal paths (solid lines) is always preferable than transport through the superconducting islands (SCIs) (see text). (b) As the magnetic field is decreased, but still $B > B_{\max}$, more SCIs appear, resulting in a decrease in available trajectories for transport (bottom solid line in (a) and bottom dashed line in (b)) and hence negative magneto-resistance. (c) At a certain field $B_{\max}$ the resistance of normal paths and paths that include SCIs is comparable, resulting in a peak in the resistance. (d) For even lower fields, $B_c < B < B_{\max}$, transport through SCIs is always favored, resulting in positive magneto-resistance.

SCI. The resistance between two (neighboring) SC sites, R_{SS} , is taken to be very small compared with Eq.(1), but still not zero and temperature dependent, in such a way that it vanishes as $T \rightarrow 0$ (distant SC sites are disconnected). The calculations of resistance were conducted with several functional forms for $R_{SS}(T)$ (power law, exponential dependence, etc.) and no qualitative difference between them was found. The resistance between a normal site and a SC site (local N-S junction) is taken to be

$$R_{NS} \propto \exp(E_c/kT), \quad (2)$$

where E_c is the charging energy of the island. For simplicity, and to avoid additional parameters, the charging energies of all islands were taken to be the same, independent of island size. It is demonstrated below that the main experimental observations can be well understood even under such an assumption [18].

The lattice is connected to electrodes (Fig. 2) and the resistance is calculated numerically using Kirchhoff's laws. The left-most and right-most links in Fig. 2 are taken to be SC, thus avoiding a strong dependence of the resistance on the properties of the edge sites. In Fig. 3 we plot the calculated resistance (on a log scale) as a function of the probability p for different temperatures. The calculations were conducted on lattices of size 25×25 (and repeated for different lattice sizes, with no qualitative difference in the results) and log-averaged over 100 realizations of disorder. A peak in the MR is

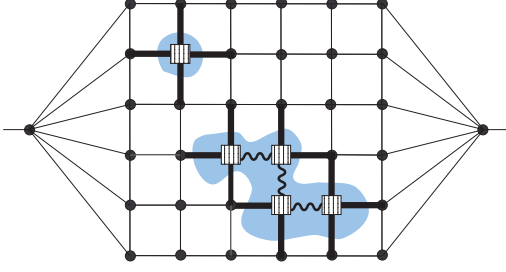


FIG. 2: The lattice model is composed of regular sites and superconducting sites. Clusters of the latter form SCIs (shaded islands). The resistance between two normal sites (small circles) is given by Eq. 1. The resistance between two SC sites (filled squares) is very small (and becomes smaller with decreasing temperature, see text) for neighboring sites (wavy lines) and is infinite (no link) between non-neighboring sites. The resistance between neighboring normal and SC sites (thick lines) is much higher than the resistance between two normal sites, and is exponential in the charging energy of the SC island (Eq. 2).

observed at $p_{\max} = 0.5$, with peak resistance four orders of magnitude larger than the resistance at the transition. The results are compared with the experimental data of [13] (inset of Fig. 3), and good qualitative agreement is evident. Notice that the critical probability, p_c , defined as the probability at which the resistance is temperature-independent, is shifted from the percolation critical probability. The reason for this is that the resistance of the SC links, R_{SS} , is finite. As the temperature is decreased the critical probability moves towards the percolation critical probability, eventually reaching it at $T = 0$.

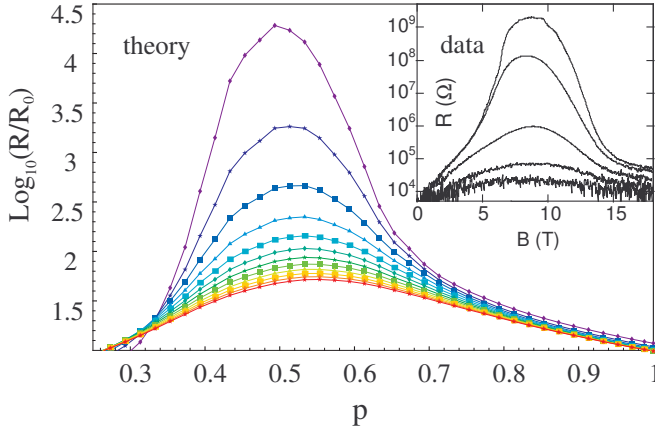


FIG. 3: Numerical results : resistance (on a log scale) as a function of probability p for different temperatures, with the parameters $W = 0.4$, $E_c = 4$, $\xi_{loc} = 0.1$, $T = 0.1, 0.2, \dots, 4$. This is to be (qualitatively) compared with the experimental data (inset) of [13].

When fitting the resistance as a function of temperature to an activation-like behavior, $R \propto \exp(T_0/T)$, we find a non-monotonic dependence of T_0 on the probability p (Fig. 4), resembling the experimental data of [13]

(upper inset of Fig. 4) and of [14]. The activation temperature rises from $T_0 \approx W$ at $p = 1$ to $T_0 \approx E_c$ for $p = p_{\max}$. It then drops back again due to increasing weight of SC areas in the sample, eventually reaching $T_0 = 0$ at the transition. Thus, in our picture T_0 is determined by the Coulomb blockade energy and not by the SC gap, as was initially suggested in [13].

At high temperatures the activation fit is excellent for all values of p . For low temperatures, on the other hand, the fit becomes worse (lower inset of Fig. 4). Similar results were presented in the experimental data of [13]. The reason for this is that at low enough temperatures tunneling into the SCIs is suppressed, except very close to the SIT. Since the resistance through normal areas is activated not by E_c but rather by W , the slope of the Arrhenius plot changes, as is also evident in the experiment. We thus predict that the low temperature behavior near B_c will be the same as in higher temperatures in strong magnetic fields $B \gg B_{\max}$.

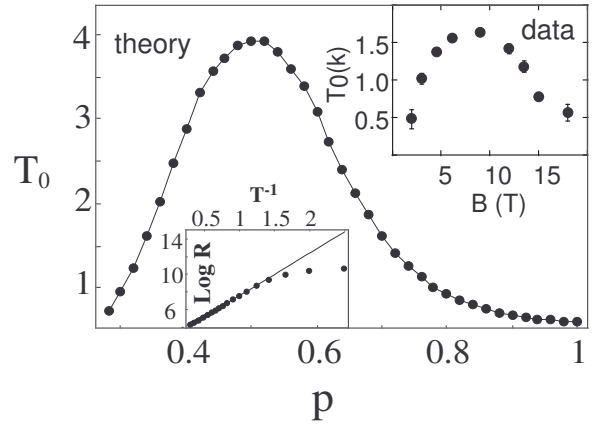


FIG. 4: The activation energy T_0 as extracted from fitting the resistance to an activation behavior, obtained from the numerical calculation and from the experimental data of [13] (inset). Lower inset : an Arrhenius plot of the resistance as a function of temperature for $p = p_{\max} = 0.5$. A deviation from an activated behavior is clearly seen.

The fact that the temperature dependence is not a pure activation in the whole magnetic field and temperature range is crucial to the observation of such a peak in the MR. If one assumes solely a magnetic field dependent activation energy, $T_0(B)$, then for different temperatures T_1 and T_2 the ratio

$$\frac{\log(R(B, T_1)/R_0)}{\log(R(B, T_2)/R_0)} = \frac{T_1/T_0(B)}{T_2/T_0(B)} = \frac{T_1}{T_2}, \quad (3)$$

would be independent of field, in contrast with the experimental observation.

The amount of disorder affects our model in several ways. First, the width of the energy distribution W increases, though this has a minor effect on the behavior near the MR peak. Second the initial concentration of

normal islands, p_0 , increases with disorder. If one assumes $p(B) \simeq p_0 + \alpha B^x$ (where α is some constant and x is probably equal to 2 for small fields, as the system is symmetric under reversal of the magnetic field direction), then $B_{\max} = (p_{\max} - p_0)^{1/x}/\alpha$, namely $B_{\max}$ decreases with increasing disorder. Lastly, the typical size of the SCIs decreases, leading to an enhancement of the Coulomb charging energy and an exponential increase of $R_{\max}$. These latter two points are consistent with the experimental observations [14], though quantitative predictions require a detailed study of the distribution of the SCIs with disorder and magnetic field (currently underway).

As mentioned in [14], at very strong fields (up to 30 T) the resistance of some samples saturates at values somewhat larger than the resistance just above the (temperature-driven) superconducting transition. Our model provides a natural explanation for this. At strong magnetic fields all vestiges of SC correlations are gone, and one is left with an insulator (which is hardly affected by magnetic field) at a lower temperature, and thus with higher resistance.

The theory presented here may also account for the MR in the presence of a tilted magnetic field [19]. Taking into account the finite width of the sample, a tilted magnetic field suppresses the SCIs both in-plane and in the "thin" direction. Due to the finite width, the electron trajectories are now 3-dimensional, and thus changes in the SCI size due to parallel magnetic field affects the resistance in a similar way as described above, leading to the same non-monotonic MR for parallel fields. This also explains the shift in the location of MR peak towards higher fields for parallel fields [19].

To summarize, we have demonstrated that competition between normal electron and Cooper-pair transport, generated by Coulomb blockade of superconducting islands and driven by perpendicular magnetic field, may yield non-monotonic magneto-resistance. This is accompanied by a change in the temperature dependence of the resistance, resulting from a crossover from nearest-neighbor hopping in normal areas to tunneling into the SC islands. This crossover may lead to a change of several orders of magnitude in the resistance, as seen experimentally.

We thank G. Sambandamurthy and D. Shahar for making their data available to us, and A. Aharony for fruitful discussions. This research has been funded by the ISF.

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- [1] P. W. Anderson, J Phys. Chem. Solids **11**, 26 (1959).
 - [2] A. A. Abrikosov and L. P. Gorkov, Zh. Eksp. Teor. Fiz. **36**, 319 (1959) [Sov. Phys. JETP **9**, 220 (1959)].
 - [3] For a review on the superconductor-insulator transition see, e.g. A. M. Goldman and N. Markovic, Phys. Today **51** (11), 39 (1998).
 - [4] S. L. Sondhi, S. M. Girvin, J. P. Carini, and D. Shahar, Rev. Mod. Phys. **69**, 315 (1997).
 - [5] M. P. A. Fisher, Phys. Rev. Lett. **65**, 923 (1990); M. Cha, M. P. A. Fisher, S. M. Girvin, M. Wallin, and A. P. Young Phys. Rev. B **44**, 6883 (1991); E. S. Sorensen, M. Wallin, S. M. Girvin, and A. P. Young, Phys. Rev. Lett. **69**, 828 (1992); M. Wallin, E. S. Sorensen, S. M. Girvin, and A. P. Young, Phys. Rev. B **49**, 12115 (1994).
 - [6] K. Das Gupta, G. Sambandamurthy, Swati S. Soman, and N. Chandrasekhar, Phys. Rev. B **63**, 104502 (2001); W. Wu and E. Bielejec, cond-mat/0310190 (2003).
 - [7] A.F. Hebard and M.A. Paalanen, Phys. Rev. Lett. **65**, 927 (1990).
 - [8] N. Mason and A. Kapitulnik, Phys. Rev. B **64**, 060504(R) (2001).
 - [9] T. I. Baturina, D. R. Islamov, J. Bentner, C. Strunk, M. R. Baklanov and A. Satta, JETP letters **79**, 337 (2004).
 - [10] Y. Dubi, Y. Meir and Y. Avishai, Phys. Rev. B **71**, 125311 (2005).
 - [11] D. Kowal and Z. Ovadyahu, Sol. St. Commun. **90**, 783 (1994).
 - [12] V. F. Gantmakher and M. V. Golubkov, Pis'ma Zh. Eksp. Teor. Fiz. **61**, 593 (1995) (JETP lett. **61**, 606 (1995)).
 - [13] G. Sambandamurthy, L. W. Engel, A. Johansson and D. Shahar, Phys. Rev. Lett. **92**, 107005 (2004).
 - [14] M. Steiner and A. Kapitulnik, cond-mat/0406227 (2004).
 - [15] S. Reich, G. Leituss, Y. Tssaba, Y. Levi, A. Sharoni and O. Millo, J. of Superconductivity **13**, 855 (2000).
 - [16] A. Ghosal, M. Randeria and N. Trivedi, Phys. Rev. Lett. **81**, 3940 (1998); A. Ghosal, M. Randeria and N. Trivedi, Phys. Rev. B **65**, 14501 (2001). See also M. A. Skvortsov, M. V. Feigel'man, cond-mat/0504002.
 - [17] A. Miller and E. Abrahams, Phys. Rev. **120**, 745 (1960).
 - [18] Even in this approximation the reasoning described in the text is valid, as a decrease in magnetic fields (at large fields, $B > B_{\max}$) leads to an increase in the number of local N-S junctions and thus to an increase in the number of paths which are characterized by a resistance given by (2). In this case $B_{\max}$ is the magnetic field where the normal resistance associated with going around a typical island is equal to R_{NS} .
 - [19] V. F. Gantmakher, M. V. Golubkov, V. T. Dolgoplov, G. E. Tsydynzhapov, and A. A. Shashkin, JETP Lett. **71**, 473 (2000); D. Shahar, private communications.